

**TITLE**

by

**Kraig Andrews**

Ph.D. Disseration Prospectus

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Advisor

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**ABSTRACT**

**TITLE HERE**

by

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August 2008

Advisor: Dr. Zhixain Zhou  
Major: Physics  
Degree: Doctor of Philosophy

Abstract here

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# Chapter 1

## Introduction

### 1.1 Background and Beginnings

Contents here, test the citation command [1]. We use the following TMDs MOS<sub>2</sub> [3, 2]

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